## ESI - GS4200 100 BAR UP TO 1500 BAR PRESSURE

General Pressure Sensor

GS4201B0400AC 10mV/V, 0..400 bar, G1/2, M12

- · Silicon-on-sapphire sensor technology
- Pressure ranges up to 1,500 bar
- · Umblemished track record of reliability
- Titanium wetted parts



## Product description

The ESI Technology GS4200 pressure sensor is designed to meet the operational requirements of demanding pressure measurement applications where good quality, fast delivery and low cost are of the highest priority.

The unique Silicon-on-Sapphire (SOS) sensor technology provides outstanding performance and gives excellent stability over a wide temperature range. The all titanium alloy wetted parts offer unbeatable corrosion resistance making it suitable for a wide range of applications. The GS4200 starts from -1 to 0 bar up to 0 to 1500 bar with a total of fourteen standard pressure ranges, four options of outputs including 4-20mA and 0-10V and also four different electrical connections including a DIN connector and M12.

This transmitter is truley unique with its versatility matched with high accuracy, impressive over pressure safety, reliability and low temperature error,

## Application examples

- Aerospace
- Automotive
- Heavy duty
- Mobile hydraulics
- Off-shore (Sea/salt water)
- Process

## Specifications

| Ambient temperature    | -4085°C                  |
|------------------------|--------------------------|
| Approvals              | CE, DNV, IEC             |
| Electrical connection  | M12                      |
| EMC                    | EN61000-6-3, EN61000-6-2 |
| Linearity              | ≤±0.25% BFSL             |
| Materials Wetted Parts | Titanium alloy           |
| Media temperature      | -50125°C                 |
| Output                 | 0-10mV/V                 |

| Overpressure protection | 800 bar             |
|-------------------------|---------------------|
| Pressure Range Max      | 400                 |
| Pressure Range Min      | 0                   |
| Pressure reference      | Gauge               |
| Process connection      | G1/2                |
| Sensor technology       | Silicon-on-Sapphire |
| Storage temperature     | 540°C               |
| Supply voltage          | 10 V DC (5-15 V)    |

